

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-014513

(43)Date of publication of application : 18.01.1990

(51)Int.Cl.

H01L 21/205

(21)Application number : 01-108376

(71)Applicant : FUJITSU LTD

(22)Date of filing : 26.04.1989

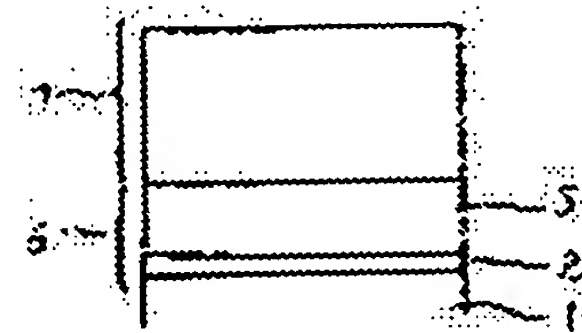
(72)Inventor : KITAHARA KUNINORI

(54) FORMATION OF COMPOUND SEMICONDUCTOR LAYER

(57)Abstract:

PURPOSE: To enhance the flatness on the surface of a compound semiconductor layer by a method wherein, after a GaAs layer has been vapor-grown at a first prescribed temperature on an Al atomic layer vapor-grown on an Si single-crystal substrate, a GaAs epitaxial layer is vapor-grown on it at a second prescribed temperature.

CONSTITUTION: An Si substrate 1 is stabilized at a prescribed temperature in an atmosphere of hydrogen; after that, trimethylaluminum(TMA) is introduced; an Al atomic layer 2 is generated on the surface. Then, the residual TMA is discharged; after that, AsH₃-hydrogen-trimethylgallium (TMG)-hydrogen constituting one cycle are introduced repeatedly. Then, a GaAs molecular layer 5 is formed on the Al atomic layer 2; after that, the introduction of the raw-material gases is stopped. Then, after a temperature has been raised and a prescribed temperature has been stabilized, TMG and AsH₃ are introduced simultaneously in the same manner as in an ordinary metal organic chemical vapor growth method; a single-crystal GaAs layer 7 of excellent flatness is grown epitaxially on the GaAs molecular layer 5. After a prescribed thickness has been reached, the introduction of the raw material gases is stopped.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]